

**AMENDMENT TO THE SPECIFICATION**

Paragraph at page 7, lines 13-26:

Referring to FIG. 3, each of substrates 32 includes a plurality of apertures 34, which allow the exhaust gas pass therethrough as it flows through CVD chamber 26 from gas inlet 28 to gas outlet 30. The number, shape and size of apertures 34 may be varied on each substrate 32 and among a number of substrates to suit a particular application, depending on design parameters such as number of substrates, amount of silane contained in the exhaust gas and velocity of exhaust gas through CVD chamber 26. In one embodiment, a substrate 32 includes nine apertures each having a diameter of 0.75 inches. Substrates 32 are preferably removably mounted within CVD chamber 26 so that they may be periodically removed, cleaned of the deposited silicon and replaced for further use. The deposited silicon may be removed from substrates 32, e.g., by chemical etching. Providing removable and reusable substrates 32 will reduce the lifetime cost of operating the CVD abatement apparatus. However, if desired, substrates 32 need not be removable. In this situation, entire enclosure 24 and substrates 32 may be disposed of when the silicon deposits on the substrates reach a maximum thickness.

Paragraph at page 16, line 15:

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